# PAPER -1

Questions Q1. to Q20. carry one mark each.

**Q1.** If  $\mathbf{A} = \begin{bmatrix} 0 & 1 & -2 \\ -1 & 0 & 3 \\ 2 & -2 & \lambda \end{bmatrix}$  is a singular matrix, then  $\lambda$  is

**Q2.** Let  $f(x) = e^x$  in [0, 1]. Then, the value of *c* of the mean-value theorem is

(A) 
$$0.5$$
 (B)  $(e-1)$   
(C)  $\log(e-1)$  (D) None

Q3. If  $\mathbf{D} = xy\mathbf{u}_x + yz\mathbf{u}_y + zx\mathbf{u}_z$ , then the value of  $\oiint \mathbf{A} \cdot d\mathbf{S}$  is, where S is the surface of the cube defined by  $0 \le x \le 1, 0 \le y \le 1, 0 \le z \le 1$ 

(A) 0.5	(B) 3
(C) 0	(D) 1.5

**Q4.** The gradient of field  $f = y^2 x + xyz$  is

(A)  $y(y+z)\mathbf{u}_x + x(2y+z)\mathbf{u}_y + xy\mathbf{u}_z$ 

(B)  $y(2x+z)\mathbf{u}_x + x(x+z)\mathbf{u}_y + xy\mathbf{u}_z$ 

- (C)  $y^2 \mathbf{u}_x + 2yx \mathbf{u}_y + xy \mathbf{u}_z$
- (D)  $y(2y+z)\mathbf{u}_x + x(2y+z)\mathbf{u}_y + xy\mathbf{u}_z$
- **Q5.** In the circuit of fig. Q5 the value of  $R_1$  will be





- Q7. Epitaxial growth is used in integrated circuit
  - (A) because it produces low parasitic capacitance
  - (B) because it yields back-to-back isolating junctions
  - (C) to grow single crystal n –doped silicon on a single-crystal p –type substrate

(D) to grow selectively single-crystal p –doped silicon of one resistivity on p –type substrate of a different resistivity.

Q8. The chemical reaction involved in epitaxial growth in IC chips takes place at a temperature of about

**Q9.** In the circuit of fig. Q9 the output voltage  $v_o$  is



(A) 2.67 V	(B) –2.67 V
(C) -6.67 V	(D) 6.67 V

**Q10.** Assertion (A) In the self bias CE transistor amplifier a single battery is used. **Reason (R)** The collector base junction is forward biased by  $V_{CC}$ .

Chose the correct option:

- (A) Both A and R individually true and R is the correct explanation of A.
- (B) Both A and R individually true and but R is not the correct explanation of A.
- (C) A is true but R is false
- (D) A is false

## **Q11.** The address bus width of a memory of size $1024 \times 8$ bits is

(A) 10 bits	(B) 13 bits
(C) 8 bits	(D) 18 bits

**Q12.** Consider the TTL circuit in fig Q12. The value of  $V_H$  and  $V_L$  are respectively





 $12 \mathrm{V}$ 

**Q21.** If the rank of the matrix, 
$$\mathbf{A} = \begin{bmatrix} 2 & -1 & 3 \\ 4 & 7 & \lambda \\ 1 & 4 & 5 \end{bmatrix}$$
 is 2, then the value of  $\lambda$  is  
(A) -13 (B) 13  
(C) 3 (D) None of these  
**Q22.** If  $u = e^{xyz}$ , then  $\frac{\partial^3 u}{\partial x \partial y \partial z}$  is equal to  
(A)  $e^{xyz} [1 + xyz + 3x^2y^2z^2]$   
(B)  $e^{xyz} [1 + xyz + x^3y^3z^3]$   
(C)  $e^{xyz} [1 + 3xyz + x^2y^2z^2]$   
(D)  $e^{xyz} [1 + 3xyz + x^3y^3z^3]$   
**Q23.** The value of  $\int e^x \left(\frac{1 + \sin x}{1 + \cos x}\right) dx$  is  
(A)  $e^x \tan \frac{x}{2} + c$  (B)  $e^x \cot \frac{x}{2} + c$   
(C)  $e^x \tan x + c$  (D)  $e^x \cot x + c$ 

**Q24.** The solution of the differential equation  $(x - y^2)dx + 2xydy = 0$  is

(A) 
$$ye^{2/x} = A$$
  
(B)  $xe^{y^2/x} = A$   
(C)  $xe^{x/y^2} = A$   
(D)  $ye^{x/y^2} = A$ 

**Q25.** The Taylor's series expansion of  $f(z) = \sin z$  about  $z = \frac{\pi}{4}$  is

$$(A) \frac{1}{\sqrt{2}} \left[ 1 + \left( z - \frac{\pi}{4} \right) - \frac{1}{2!} \left( z - \frac{\pi}{4} \right)^2 - \dots \right]$$
  

$$(B) \frac{1}{\sqrt{2}} \left[ 1 + \left( z - \frac{\pi}{4} \right) + \frac{1}{2!} \left( z - \frac{\pi}{4} \right)^2 + \dots \right]$$
  

$$(C) \frac{1}{\sqrt{2}} \left[ 1 - \left( z - \frac{\pi}{4} \right) - \frac{1}{2!} \left( z - \frac{\pi}{4} \right)^2 - \dots \right]$$

(D) None of the above

Diameter of heart (in mm)	Number of persons
120	5
121	9
122	14
123	8
124	5
125	9

The median of the above frequency distribution is

(A) 122 mm	(B) 123 mm

Q27. For  $\frac{dy}{dx} = x + y^2$ , given that y = 0 at x = 0, using Picard's method up to third order of approximation the solution of the differential equation is

(D) 122.75 mm

(A) 
$$\frac{x^2}{2} + \frac{x^5}{40} + \frac{x^8}{480} + \frac{x^{11}}{1600}$$
  
(B)  $\frac{x^2}{2} + \frac{x^5}{20} + \frac{x^8}{160} + \frac{x^{11}}{4400}$   
(C)  $\frac{x^2}{2} + \frac{x^5}{20} + \frac{x^8}{160} + \frac{x^{11}}{2400}$   
(D)  $\frac{x^2}{2} + \frac{x^5}{40} + \frac{x^8}{480} + \frac{x^{11}}{2400}$ 

(C) 122.5 mm

**Q28.** The bilateral laplace transform of  $\cos 3t u(-t) * e^{-t} u(t)$  is

(A) 
$$\frac{-s}{(s+1)(s^2+9)}$$
, Re  $(s) > 0$   
(B)  $\frac{-s}{(s+1)(s^2+9)}$ ,  $-1 < \text{Re}(s) < 0$   
(C)  $\frac{s}{(s+1)(s^2+9)}$ ,  $-1 < \text{Re}(s) < 0$   
(D)  $\frac{s}{(s+1)(s^2+9)}$ , Re  $(s) > 0$ 

**Q29.** The *z*-transform of  $x[n] = \left(\frac{2}{3}\right)^{|n|}$  is

(A) 
$$\frac{-5z}{(2z-3)(3z-2)}$$
,  $-\frac{3}{2} < z < -\frac{2}{3}$   
(B)  $\frac{-5z}{(2z-3)(3z-2)}$ ,  $\frac{2}{3} < |z| < \frac{3}{2}$   
(C)  $\frac{5z}{(2z-3)(3z-2)}$ ,  $\frac{2}{3} < |z| < \frac{2}{3}$   
(D)  $\frac{5z}{(2z-3)(3z-2)}$ ,  $-\frac{3}{2} < z < -\frac{2}{3}$ 

Q30. Consider the graph shown in fig. Q30 in which twigs are solid line and links are dotted line.



A fundamental loop matrix for this tree is given as below

$$\mathbf{B}_{F} = \begin{bmatrix} 1 & 0 & 0 & 1 & 0 & 1 \\ 0 & 1 & 0 & -1 & -1 & 0 \\ 0 & 0 & 1 & 0 & 1 & -1 \end{bmatrix}$$

The oriented graph will be







## Q31. The value of the current measured by the ammeter in Fig. Q31 is



Q32. In the circuit of fig. Q32 the equivalent resistance seen by the capacitor is



**Q33.** In the circuit of fig. Q33 switch is moved from position *a* to *b* at t = 0. The  $i_L(t)$  for t > 0 is



(A)  $(4-6t)e^{4t}$  A (B)  $(3-6t)e^{-4t}$  A

(C)  $(3-9t)e^{-5t}$  A (D)  $(3-8t)e^{-5t}$  A

**Q34.** In the circuit of fig. Q34 the i(t) will be



(A) $2\sin(2t+5.77^{\circ})$ A	(B) $\cos(2t - 84.23^\circ)$ A
(A) $2\sin(2t+5.77^\circ)$ A	(B) $\cos(2t - 84.23^\circ)$ A

(C) $2\sin(2t-5.77^{\circ})$ A	(D) $\cos(2t + 84.23^\circ)$ A
--------------------------------	--------------------------------

**Q35.** In the circuit of fig. Q35  $L_{eq}$  will be



(C) 3 H (D) 4 H





- Q37. Three scattering mechanism exist in a semiconductor. If only the first mechanism were present, the mobility would be 500 cm<sup>2</sup>/V s. If only the second mechanism were present, the mobility would be 750 cm<sup>2</sup>/V s. If only third mechanism were present, the mobility would be 1500 cm<sup>2</sup>/V s. The net mobility is
  - (A) 2750 cm<sup>2</sup>/V s
  - (B) 1114 cm<sup>2</sup>/V s
  - (C) 818 cm<sup>2</sup>/V s
  - (D) 250 cm<sup>2</sup>/V s
- **Q38.** In a silicon  $(n_i = 1.5 \times 10^{10} \text{ cm}^{-3}, D_n = 35 \text{ cm}^2/\text{s})$  sample the electron concentration drops linearly from  $10^{18} \text{ cm}^{-3}$  to  $10^{16} \text{ cm}^{-3}$  over a length of 2.0 µm. The current density due to the electron diffusion current is
  - (A)  $9.3 \times 10^4$  A/cm<sup>2</sup>
  - (B)  $2.8 \times 10^4$  A/cm<sup>2</sup>
  - (C)  $9.3 \times 10^9$  A/cm<sup>2</sup>
  - (D)  $2.8 \times 10^9$  A/cm<sup>2</sup>
- **Q39.** A *pn* junction diode is operating in reverse bias region. The applied reverse voltage, at which the ideal reverse current reaches 90% of its reverse saturation current, is
  - (A) -59.6 mV
  - (B) 2.7 mV
  - (C) 4.8 mV
  - (D) 42.3 mV
- **Q40.** In bipolar transistor biased in the forward-active region the base current is  $I_B = 50 \,\mu\text{A}$  and the collector currents is  $I_C = 2.7 \,\text{mA}$ . The  $\alpha$  is
  - (A) 0.949
  - (B) 54
  - (C) 0.982
  - (D) 0.018

- **Q41.** An *n*-channel silicon  $(n_i = 1.5 \times 10^{10} \text{ cm}^{-3})$  JFET at T = 300 K has doping concentration of  $N_d = 8 \times 10^{16} \text{ cm}^{-3}$  and  $N_a = 3 \times 10^{18} \text{ cm}^{-3}$ . The channel thickness dimensions is  $a = 0.5 \mu \text{m}$ . If the undepleted channel has to be  $0.2 \mu \text{m}$ , the required gate voltage is
  - (A) 2.73 V
  - (B) -2.73 V
  - (C) 4.66 V
  - (D) -4.66 V

(A) 1.04 mA

(C) 962 µA

**Q42.** In the circuit shown in fig. Q42 voltage  $V_E = 4$  V. The value of  $\alpha$  and  $\beta$  are respectively



(A) 0.943, 17.54	(B) 0.914, 17.54
(C) 0.914, 10.63	(D) 0.914, 11.63

**Q43.** In the current mirror circuit of fig. Q43 the transistor parameters are  $V_{BE} = 0.7 \text{ V}, \beta = 50$  and the Early voltage is infinite. Assume transistor are matched. The output current  $I_{a}$  is



**Q44.** The parameter of the transistor in fig. Q44 are  $V_{TN} = 1.2 \text{ mA} / \text{V}^2$ ,  $K_n = 0.5 \text{ mA} / \text{V}^2$ , and  $\lambda = 0$ . The voltage  $V_{DS}$  is



Q45. In the circuit shown in fig. Q45 the op-amp is ideal. If transistor has  $\beta = 60$ , then the total current supplied by the 15 V source is



(C) 49.4 mA (D) 168 mA

**Q46.** Consider the statements below:

(A) 123.1 mA

1. If the output waveform from an OR gate is the same as the waveform at one of its inputs, the other input is being held permanently LOW.

**2.** If the output waveform from an OR gate is always HIGH, one of its input is being held permanently HIGH.

The statement, which is always true, is

(A) Both 1 and 2	(B) Only 1
(C) Only 2	(D) None of the above

**Q47.** A logic circuit consist of two  $2 \times 4$  decoder as shown in fig. Q47.



The output of decoder are as follow

 $D_{0} = 1 \text{ when } A_{0} = 0, \quad A_{1} = 0$   $D_{1} = 1 \text{ when } A_{0} = 1, \quad A_{1} = 0$   $D_{2} = 1 \text{ when } A_{0} = 0, \quad A_{1} = 1$   $D_{3} = 1 \text{ when } A_{0} = 1, \quad A_{1} = 1$ The value of f(x, y, z) is
(A) 0
(B) z
(C)  $\overline{z}$ (D) 1

Q48. The circuit shown in fig. Q48 implements the function



(A)  $ABC + \overline{ABC}$ 

(B)  $ABC + \overline{(A+B+C)}$ 

(C)  $\overline{ABC} + \overline{(A+B+C)}$ 

<sup>(</sup>D) None of the above

Q49. Consider the following 8085 assembly program

	MVI	A, DATA1
	MOV	B, A
	SUI	51H
	JC	DLT
	MOV	A, B
	SUI	82H
	JC	DSPLY
DLT :	XRA	А
	OUT PORT1	
	HLT	
DSPLY :	MOV	A, B
	OUT PORT2	
	HLT	

This program will display

- (A) the bytes from 51H to 82H at PORT2
- (B) 00H AT PORT1
- (C) all byte at PORT1
- (D) the bytes from 52H to 81H at PORT 2

# **Q50.** Consider the following program

MVI A, BYTE1 RRC RRC

If BYTE1 = 32H, the contents of A after the execution of program will be

- (A) 08H (B) 8CH
- (C) 12H (D) None of the above
- **Q51.** The response of a system S to a complex input  $x(t) = e^{j5t}$  is specified as  $y(t) = te^{j5t}$ . The system
  - (A) is definitely LTI (B) is definitely not LTI
  - (C) may be LTI (D) information is insufficient

Q52. The following input output pairs have been observed during the operation of a time invariant system :

The conclusion regarding the linearity of the system is

- (A) System is linear
- (B) System is not linear
- (C) One more observation is required.
- (D) Conclusion cannot be drawn from observation.
- **Q53.** The transfer function H(s) of a stable system is

$$H(s) = \frac{s^2 + 5s - 9}{(s+1)(s^2 - 2s + 10)}$$

The impulse response is

(A) 
$$-e^{-t}u(t) + (e^{t}\sin 3t + 2e^{t}\cos 3t)u(t)$$
  
(B)  $-e^{-t}u(t) - (e^{t}\sin 3t + 2e^{t}\cos 3t)u(-t)$   
(C)  $-e^{-t}u(t) - (e^{t}\sin 3t + 2e^{t}\cos 3t)u(t)$   
(D)  $-e^{-t}u(t) + (e^{t}\sin 3t + 2e^{t}\cos 3t)u(-t)$ 

Q54. The frequency response which has nonlinear phase is

(A) 
$$\frac{1}{j\omega+1}$$
 (B)  $\frac{1}{(j\omega+1)^2}$   
(C)  $\frac{1}{(j\omega+1)(j\omega+2)}$  (D) All above

$$x[n] = \frac{\sin\left(\frac{1\,\ln n}{20}\,n\right)}{\sin\left(\frac{\pi}{20}\,n\right)}$$

with a fundamental period N = 20. The Fourier series coefficients of this function are

(A) 
$$\frac{1}{20}(u[k+5]-u[k-6]), |k| \le 10$$
  
(B)  $\frac{1}{20}(u[k+5]-u[k-5]), |k| \le 10$   
(C)  $(u[k+5]-u[k+6]), |k| \le 10$   
(D)  $(u[k+5]-u[k-6]), |k| \le 10$ 

**Q56.** A feedback control system shown in fig. Q56 is subjected to noise N(s).



The noise transfer function  $\frac{C_N(s)}{N(s)}$  is

(A) 
$$\frac{G_1 G_2}{1 + G_1 G_2 H}$$
 (B)  $\frac{G_2}{1 + G_1 H}$ 

(C) 
$$\frac{G_2}{1+G_2H}$$
 (D) None of the above

**Q57.** For the block diagram shown in the fig. Q57 the limiting value of K for stability of inner loop is found to be X < K < Y. The over all system will be stable if and only if



**Q58.** The transfer function of a *ufb* system is

$$G(s) = \frac{10^5(s+3)(s+10)(s+20)}{s(s+25)(s+a)(s+30)}$$

The value of *a* to yield velocity error constant  $K_v = 10^4$  is

- (C) 8 (D) 16
- **Q59.** The forward-path transfer function of a *ufb* system is  $G(s) = \frac{K(s+\alpha)(s+3)}{s(s^2-1)}$ . The root-loci for K > 0 with  $\alpha = 5$  is







The transfer function is

(A)  $\frac{8s(s+2)}{(s+5)(s+10)}$ (B)  $\frac{4(s+5)}{(s+2)(s+10)}$ (C)  $\frac{4(s+2)}{s(s+5)(s+10)}$ (D)  $\frac{8s(s+5)}{(s+2)(s+10)}$ 

## Q61. The joint PDF of random variable x and y is shown in fig. Q61. The value of A is



(A) 1 (B) 2

(C) 4 (D) None of the above

Q62. The probability density function of a random variable X is given as  $f_X(x)$ . A random variable Y is defined as y = ax + b where a < 0. The PDF of random variable Y is

(A) 
$$bf_{X}\left(\frac{y-b}{a}\right)$$
  
(B)  $af_{X}\left(\frac{y-b}{a}\right)$   
(C)  $\frac{1}{a}f_{X}\left(\frac{y-b}{a}\right)$   
(D)  $\frac{1}{b}f_{X}\left(\frac{y-b}{a}\right)$ 

**Q63.** A carrier is amplitude modulate to 100 % by a polar rectangular signal as shown in fig. Q62. The percentage increase in signal power is



**Q64.** In a AM signal the received signal power is  $10^{-10}$  W with a maximum modulating signal of 5 kHz. The noise spectral density at the receiver input is  $10^{-18}$  W/Hz. If the noise power is restricted to the message signal bandwidth only, the signals-to-noise ratio at the input to the receiver is



(C) 56 dB (D) 33 dB

**Q65.** Fig. Q65 shows a PCM signals in which amplitude level of +1 volt and -1 volt are used to represent binary symbol 1 and 0 respectively. The code word used consists of three bits.



The sampled version of analog signal from which this PCM signal is derived is

(A) 4 5 2 1 3
(B) 8 4 3 1 2
(C) 6 4 3 1 7
(D) 1 2 3 4 5

**Q66.** The flux of  $\mathbf{D} = \rho^2 \cos^2 \phi \mathbf{u}_{\rho} + 3\sin \phi \mathbf{u}_{\phi}$  over the closed surface of the cylinder  $0 \le z < 3$ ,  $\rho = 3$  is

- (A) 324 (B) 81π
- (C) 81 (D)  $64\pi$
- **Q67.** In a certain region  $\mathbf{J} = (4y\mathbf{u}_x + 2xz\mathbf{u}_y + z^3\mathbf{u}_z)\sin(10^4 t)$  A/m. If volume charge density  $\rho_v$  in z = 0 plane is zero, then  $\rho_v$  is
  - (A)  $3z^2 \cos(10^4 t) \text{ mC/m}^3$
  - (B)  $0.3z^2 \cos(10^4 t) \,\mathrm{mC/m^3}$
  - (C)  $-3z^2 \cos(10^4 t) \,\mathrm{mC/m^3}$
  - (D)  $-0.3z^2 \cos(10^4 t) \text{ mC/m}^3$
- **Q68.** Two  $\lambda/4$  transformer in tandem are to connect a 50  $\Omega$  line to a 75  $\Omega$  load as shown in fig. Q68. If  $Z_{02} = 30\Omega$  and there is no reflected wave to the left of A, then the characteristic impedance  $Z_{01}$  is



**Q69.** The cross section of a waveguide is shown in fig. Q69. It has dielectric discontinuity as shown in fig. If the guide operate at 8 GHz in the dominant mode, the standing wave ratio is



**Q70.** An antenna consists of 4 identical Hertizian dipoles uniformly located along the z-axis and polarized in the z-direction. The spacing between the dipole is  $\frac{\lambda}{4}$ . The group pattern function is

(A) 
$$4\cos\left(\frac{\pi}{4}\cos\theta\right)\cos\left(\frac{\pi}{2}\cos\theta\right)$$
 (B)  $4\cos\left(\frac{\pi}{4}\cos\theta\right)\cos\left(\frac{\pi}{8}\cos\theta\right)$   
(C)  $4\cos\left(\frac{\pi}{4}\cos\theta\right)\sin\left(\frac{\pi}{2}\cos\theta\right)$  (D)  $4\cos\left(\frac{\pi}{4}\cos\theta\right)\sin\left(\frac{\pi}{8}\cos\theta\right)$ 

#### **Common Data Questions**

#### **Common Data for Questions Q71-73:**

In the voltage regulator circuit in fig. Q71-73 the Zener diode current is to be limited to the range  $5 \le i_z \le 100 \text{ mA}$ .



**Q71.** The range of possible load current is

(A) $5 \le i_L \le 130 \mathrm{mA}$	(B) $25 \le i_L \le 120 \mathrm{mA}$
-------------------------------------	--------------------------------------

- (C)  $10 \le i_L \le 110 \text{ mA}$  (D) None of the above
- **Q72.** The range of possible load resistance is

$(A) 60 \le R_L \le 372 \Omega$	(B) $60 \le R_L \le 200 \Omega$
(C) $40 \le R_L \le 192 \Omega$	(D) $40 \le R_L \le 360 \Omega$

Q73. The power rating required for the load resistor is

(A) 576 mW	(B) 360 µW
(C) 480 mW	(D) 75 µW

## **Common Data for Questions Q74-75:**

The state-space representation of a system is given by  $\dot{\mathbf{x}}(t) = \mathbf{A} \cdot \mathbf{x}(t) + \mathbf{B} \cdot \mathbf{u}(t)$ , where

$$\mathbf{A} = \begin{bmatrix} 0 & 2 \\ -2 & 0 \end{bmatrix}, \mathbf{B} = \begin{bmatrix} 0 \\ 1 \end{bmatrix}$$

If  $\mathbf{x}(0)$  is the initial state vector, and the component of the input vector  $\mathbf{u}(t)$  are all unit step function, then the state transition equation is given by  $\dot{\mathbf{x}}(t) = \Phi(t)\mathbf{x}(0) + \theta(t)$ , where  $\Phi(t)$  is a state transition matrix and  $\theta(t)$  is a vector matrix.

**Q74.** The  $\Phi(t)$  is

(A) 
$$\begin{bmatrix} \cos 2t & \sin 2t \\ -\sin 2t & \cos 2t \end{bmatrix}$$
  
(B)  $\begin{bmatrix} \cos 2t & -\sin 2t \\ \sin 2t & \cos 2t \end{bmatrix}$   
(C)  $\begin{bmatrix} \sin 2t & \cos 2t \\ -\cos 2t & \sin 2t \end{bmatrix}$   
(D)  $\begin{bmatrix} \sin 2t & -\cos 2t \\ \cos 2t & \sin 2t \end{bmatrix}$ 

**Q75.** The  $\theta(t)$  is

(A) 
$$\begin{bmatrix} 0.5(1 - \sin 2t) \\ 0.5\cos 2t \end{bmatrix}$$
 (B)  $\begin{bmatrix} \sin 2t \\ \cos 2t \end{bmatrix}$   
(C)  $\begin{bmatrix} 0.5(1 - \cos 2t) \\ 0.5\sin 2t \end{bmatrix}$  (D)  $\begin{bmatrix} \cos 2t \\ \sin 2t \end{bmatrix}$ 

Linked Answer Questions: Q76. to Q85. carry two marks each.

#### **Statement for Linked Answer Questions: Q76. and Q77:**

A silicon Hall device at T = 300 K has the geometry  $d = 10^{-3}$  cm ,  $W = 10^{-2}$  cm,  $L = 10^{-1}$  cm. The following parameters are measured:  $I_x = 0.75$  mA,  $V_x = 15$  V,  $V_H = +5.8$  mV,  $B_z = 0.1$  tesla.

**Q76.** The majority carrier concentration is

(A)  $8 \times 10^{15}$  cm<sup>-3</sup>, *n*-type

- (B)  $8 \times 10^{15} \text{ cm}^{-3}$ , *p*-type
- (C)  $4 \times 10^{15}$  cm<sup>-3</sup>, *n*-type
- (D)  $4 \times 10^{15}$  cm<sup>-3</sup>, *p*-type
- Q77. The majority carrier mobility is
  - (A)  $430 \text{ cm}^2/\text{V}-\text{s}$  (B)  $215 \text{ cm}^2/\text{V}-\text{s}$
  - (C)  $390 \text{ cm}^2/\text{V}-\text{s}$  (D)  $195 \text{ cm}^2/\text{V}-\text{s}$

#### Statement for Linked Answer Questions: Q78 and Q79:

Consider the circuit shown in fig. Q78-79.



**Q78.** The expression for the next state  $Q^+$  is

(A) xQ B)  $x\overline{Q}$ (C)  $x \oplus Q$  (D)  $x \odot Q$ 

**Q79.** Let the clock pulses be numbered 1, 2, 3... after the point at which the FF is reset ( $Q_0 = 0$ ). The circuit is a

- (A) even parity checker (B) odd parity generator
- (C) Both A and B (D) None of the above

## Statement for Linked Answer Questions: Q80 and Q81:

A causal and stable LTI system has the property that  $\left(\frac{2}{3}\right)^n u[n] \implies n\left(\frac{2}{3}\right)^n u[n]$ .

**Q80.** The frequency response  $H(e^{j\Omega})$  for this system is

(A) 
$$\frac{2e^{j\Omega}}{2-3e^{j\Omega}}$$
 (B)  $\frac{2e^{-j\Omega}}{2-3e^{-j\Omega}}$   
(C)  $\frac{2e^{j\Omega}}{3-2e^{j\Omega}}$  (D)  $\frac{2e^{-j\Omega}}{3-2e^{j\Omega}}$ 

**Q81.** The difference equation for this system relating any input x[n] and the corresponding output y[n] is

(A) 3y[n] - 2y[n-1] = 2x[n](B) 3y[n] - 2y[n-1] = 2x[n-1](C) 3y[n] - 2y[n+1] = 2x[n+1]

(D) 
$$3y[n] - 2[y+1] = 2x[n]$$

## Statement for Linked Answer Questions: Q82 and Q83:

In a certain frequency–modulation experiment conducted with  $f_m = 1 \text{ kHz}$  and increasing amplitude (starting from 0 V), it is found that the carrier component of the FM signal is reduced to zero for the first time when  $A_m = 2$  V. Given that Bessel function  $J_0(x)$  is zero for x = 2.44, 5.52, 8.65, 11.8 and so on.

Q82. The frequency sensitivity of the modulator is

(A) 1.38 kHz/V	(B) $0.61  \mathrm{kHz/V}$
(C) 2.76 kHz/V	(D) 1.22 kHz/V

**Q83.** The carrier components is reduced to zero for the second time for the value of  $A_m$ 

(A) 4.52 V	(B) 3.38 V
(C) 2.68 V	(D) 1.39 V

# Statement for Linked Answer Questions: Q84 and Q85:

The amplitude of a wave traveling through a lossy nonmagnetic medium reduces by 18% every meter. The wave operates at 10 MHz and the electric field leads the magnetic field by 24°.

- **Q84.** The propagation constant is
  - (A) 0.198 + j0.448 per meter
  - (B) 0.346 + j0.713 per meter
  - (C) 0.448 + j0.198 per meter
  - (D) 0.713 + j0.346 per meter

### **Q85.** The skin depth is

- (A) 2.52 m (B) 5.05 m
- (C) 8.46 m (D) 4.23 m

(C)
. (A)
. (D)
. (D)
. (A)
. (D)
. (D)
. (C)
. (C)
. (B)
. (A)
. (C)
. (D)
. (A)
. (C)
. (D)
. (B)

26 Paper-1